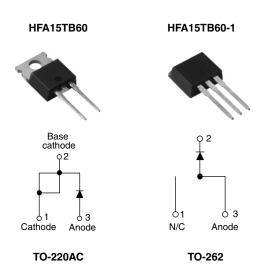


Vishay High Power Products

HEXFRED® Ultrafast Soft Recovery Diode, 15 A



| PRODUCT SUMMARY | | | | |
|---------------------------------|----------|--|--|--|
| V_{R} | 600 V | | | |
| V _F at 15 A at 25 °C | 1.7 V | | | |
| I _{F(AV)} | 15 A | | | |
| t _{rr} (typical) | 19 ns | | | |
| T _J (maximum) | 150 °C | | | |
| Q _{rr} | 84 nC | | | |
| dI _{(rec)M} /dt | 188 A/μs | | | |

FEATURES

- Ultrafast recovery
- Ultrasoft recovery
- Very low I_{RRM}
- Very low Q_{rr}
- · Specified at operating conditions
- · Designed and qualified for industrial level

BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- · Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION

HFA15TB60 is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 15 A continuous current, the HFA15TB60 is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the th portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED HFA15TB60 is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

| ABSOLUTE MAXIMUM RATINGS | | | | | |
|--------------------------------------------------|-----------------------------------|-------------------------|---------------|-------|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS | |
| Cathode to anode voltage | V _R | | 600 | V | |
| Maximum continuous forward current | l _F | T _C = 100 °C | 15 | | |
| Single pulse forward current | I _{FSM} | | 150 | Α | |
| Maximum repetitive forward current | I _{FRM} | | 60 | | |
| Maximum navver discination | P _D | T _C = 25 °C | 74 | W | |
| Maximum power dissipation | | T _C = 100 °C | 29 | - vv | |
| Operating junction and storage temperature range | T _J , T _{Stg} | | - 55 to + 150 | °C | |

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HFA15TB60/HFA15TB60-1

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Revision: 30-Jul-08

| ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified) | | | | | | | |
|--------------------------------------------------------------------------------------|-----------------|------------------------------------------------------------------------|------------|------|------|------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN. | TYP. | MAX. | UNITS |
| Cathode to anode breakdown voltage | V _{BR} | Ι _R = 100 μΑ | | 600 | - | - | |
| | | I _F = 15 A | | - | 1.3 | 1.7 | V |
| Maximum forward voltage V | V_{FM} | I _F = 30 A | See fig. 1 | = | 1.5 | 2.0 | |
| | | I _F = 15 A, T _J = 125 °C | | - | 1.2 | 1.6 | |
| Maximum reverse | | $V_R = V_R$ rated | See fig. 2 | - | 1.0 | 10 | |
| leakage current | I _{RM} | $T_J = 125 ^{\circ}\text{C}, V_R = 0.8 \text{x} V_R \text{rated}$ | See lig. 2 | - | 400 | 1000 | μΑ |
| Junction capacitance | C _T | V _R = 200 V | See fig. 3 | = | 25 | 50 | pF |
| Series inductance | L _S | Measured lead to lead 5 mm from package body | | - | 8.0 | - | nH |

| DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified) | | | | | | | |
|---------------------------------------------------------------------------------------------|---------------------------|--------------------------------------------------------------------------------|----------------------------------------------------------------------------------------|------|------|------|--------|
| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN. | TYP. | MAX. | UNITS |
| | t _{rr} | $I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$ | | - | 19 | - | |
| Reverse recovery time See fig. 5 | t _{rr1} | T _J = 25 °C | | - | 42 | 60 | ns |
| occ lig. 5 | t _{rr2} | T _J = 125 °C | | - | 74 | 120 | |
| Peak recovery current See fig. 6 | I _{RRM1} | T _J = 25 °C | $I_F = 15 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$ | - | 4.0 | 6.0 | А |
| | I _{RRM2} | T _J = 125 °C | | - | 6.5 | 10 | |
| Reverse recovery charge | Q _{rr1} | T _J = 25 °C | | - | 84 | 180 | nC |
| See fig. 7 | Q _{rr2} | T _J = 125 °C | | - | 241 | 600 | 110 |
| Peak rate of fall of recovery current during t _b See fig. 8 | dI _{(rec)M} /dt1 | T _J = 25 °C | | - | 188 | - | - A/μs |
| | dI _{(rec)M} /dt2 | T _J = 125 °C | | - | 160 | - | |

| THERMAL - MECHANICAL SPECIFICATIONS | | | | | | |
|-----------------------------------------|-------------------|--------------------------------------------|--------------|------|------------|------------------------|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS |
| Lead temperature | T _{lead} | 0.063" from case (1.6 mm) for 10 s | - | - | 300 | °C |
| Thermal resistance, junction to case | R _{thJC} | | - | - | 1.7 | |
| Thermal resistance, junction to ambient | R _{thJA} | Typical socket mount | - | - | 80 | K/W |
| Thermal resistance, case to heatsink | R _{thCS} | Mounting surface, flat, smooth and gerased | - | 0.5 | - | |
| Waight | | | - | 2.0 | - | g |
| Weight | | | - | 0.07 | - | OZ. |
| Mounting torque | | | 6.0 (5.0) | - | 12 (10) | kgf · cm (lbf · in) |
| Marking device | | Case style TO-220AC | HFA15TB60 | | | |
| | | Case style TO-262 | HFA15TB60-1 | | | |

For technical questions, contact: diodes-tech@vishay.com

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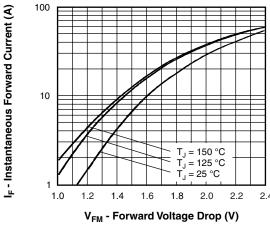


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

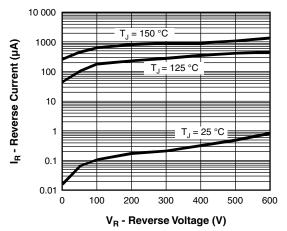


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

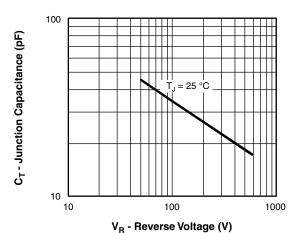


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

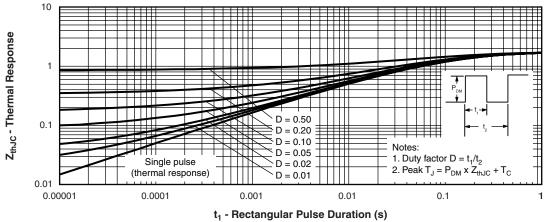


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

HFA15TB60/HFA15TB60-1

Vishay High Power Products HEXFRED® Ultrafast Soft Recovery Diode, 15 A



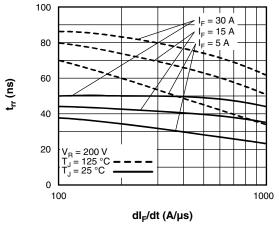


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

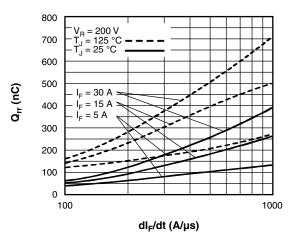


Fig. 7 - Typical Stored Charge vs. dI_F/dt

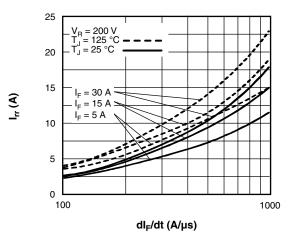


Fig. 6 - Typical Recovery Current vs. dl_F/dt

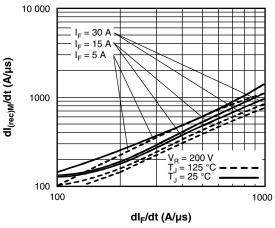


Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt



HEXFRED® V Ultrafast Soft Recovery Diode, 15 A

Vishay High Power Products

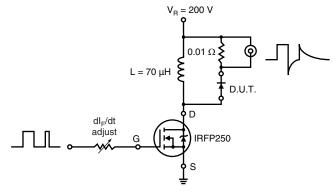
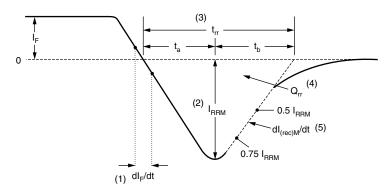


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt rate of change of current through zero crossing
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}
- (2) I_{RRM} peak reverse recovery current
- $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RBM} and 0.50 I_{RBM} extrapolated to zero current.
- (5) $dI_{(rec)M}/dt$ peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

| LINKS TO RELATED DOCUMENTS | | | | |
|--------------------------------------------|---------------------------------|--|--|--|
| Dimensions http://www.vishay.com/doc?95261 | | | | |
| Part marking information | http://www.vishay.com/doc?95262 | | | |



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